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AN/"Nantero Inc": 244 patents.

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PAT. NO.	Title
1 11,072,714	Nanotube solution treated with molecular additive, nanotube film having enhanced adhesion property, and methods for forming the nanotube solution and the nanotube film
2 11,037,624	Devices for programming resistive change elements in resistive change element arrays
3 10,937,498	Methods for programing DDR compatible open architecture resistive change element arrays
4 10,937,497	Methods for accessing 1-R resistive change element arrays
5 10,885,978	Nonvolatile nanotube switches with reduced switching voltages and currents
6 10,854,243	Nonvolatile nanotube memory arrays using nonvolatile nanotube blocks and cell selection transistors
7 10,825,516	Resistive change element cells sharing selection devices
8 10,773,960	Low porosity nanotube fabric articles
9 10,762,961	Resistive change element arrays using a reference line
10 10,741,761	Methods of making sealed resistive change elements
11 10,714,537	Logic elements comprising carbon nanotube field effect transistor (CNTFET) devices and methods of making same
12 10,700,131	Non-linear resistive change memory cells and arrays
13 10,661,304	Microfluidic control surfaces using ordered nanotube fabrics
14 10,654,718	Scalable nanotube fabrics and methods for making same
15 10,546,859	Double density nonvolatile nanotube switch memory cells
16 10,529,422	Method for programming 1-R resistive change element arrays
17 10,446,228	Devices and methods for programming resistive change elements
18 10,403,683	Methods for forming crosspoint arrays of resistive change memory cells
19 10,387,244	Methods for error correction with resistive change element arrays
20 10,355,206	Sealed resistive change elements
21 10,340,005	Resistive change element arrays with in situ initialization
22 10,339,982	Memory elements and cross point switches and arrays of same using nonvolatile nanotube blocks

